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- Low Input Bias Current . . . 50 pA Typ
- Low Input Noise Current 0.01 pA/√Hz Typ
- Low Supply Current . . . 4.5 mA Typ
- High Input impedance . . .  $10^{12} \Omega$  Typ
- Internally Trimmed Offset Voltage
- Wide Gain Bandwidth . . . 3 MHz Typ
- High Slew Rate . . . 13 V/μs Typ

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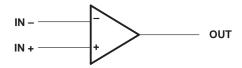
## description

This device is a low-cost, high-speed, JFET-input operational amplifier with very low input offset voltage and a specified maximum input offset voltage drift. It requires low supply current yet maintains a large gain bandwidth product and a fast slew rate. In addition, the matched high-voltage JFET input provides very low input bias and offset currents.

The LF412C can be used in applications such as high-speed integrators, digital-to-analog converters, sample-and-hold circuits, and many other circuits.

The LF412C is characterized for operation from 0°C to 70°C.

## symbol (each amplifier)



### **AVAILABLE OPTIONS**

	V <sub>IO</sub> max AT 25°C	PACKAGE			
TA		SMALL OUTLINE (D)	PLASTIC DIP (P)		
0°C to 70°C	3 mV	LF412CD	LF412CP		

The D packages are available taped and reeled. Add the suffix R to the device type (ie., LF412CDR).

# absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V <sub>CC+</sub>	
Supply voltage, V <sub>CC</sub>	18 V
Differential input voltage, V <sub>ID</sub>	±30 V
Input voltage, V <sub>I</sub> (see Note 1)	±15 V
Duration of output short circuit	unlimited
Continuous total power dissipation	500 mW
Operating temperature range	0°C to 70°C
Storage temperature range	65°C to 150°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260°C

NOTE 1: Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply voltage.

# LF412C DUAL JFET-INPUT OPERATIONAL AMPLIFIER

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## recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V <sub>CC+</sub>	3.5	18	V
Supply voltage, V <sub>CC</sub> _	-3.5	-18	V

# electrical characteristics over operating free-air temperature range, $V_{CC\pm}$ = $\pm 15$ V (unless otherwise specified)

PARAMETER		TEST CONDITIONS		T <sub>A</sub> †	MIN	TYP	MAX	UNIT
VIO	Input offset voltage	V <sub>IC</sub> = 0,	R <sub>S</sub> = 10 kΩ	25°C		1	3	mV
αΛΙΟ	Average temperature coefficient of input offset voltage	V <sub>IC</sub> = 0,	R <sub>S</sub> = 10 kΩ			10	20‡	μV/°C
IIO	Input offset current§	VIC = 0		25°C		25	100	pА
				70°C			4	nA
I <sub>IB</sub>	Input bias current§	V-2 = 0		25°C		50	200	pА
		VIC = 0	70°C			8	nA	
VICR	Common-mode input voltage range				±11	-11.5 to 14.5		V
Vом	Maximum peak output voltage swing	$R_L = 10 \text{ k}\Omega$			±12	±13.5		V
Δ. σ	Large-signal differential voltage	$V_O = \pm 10 \text{ V},  R_L = 2 \text{ k}\Omega$		25°C	25	200		V/mV
AVD				Full range	15	200		
rį	Input resistance	T <sub>A</sub> = 25°C				1012		Ω
CMRR	Common-mode rejection ratio	$R_S \le 10 \text{ k}\Omega$			70	100		dB
ksvr	Supply-voltage rejection ratio	See Note 2			70	100		dB
Icc	Supply current		·			4.5	6.8	mA

<sup>†</sup> Full range is 0°C to 70°C.

# operating characteristics, $V_{CC\pm}$ = ±15 V, $T_A$ = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V <sub>O1</sub> /V <sub>O2</sub>	Crosstalk attenuation	f = 1 kHz			120		dB
SR	Slew rate			8	13		V/μs
B <sub>1</sub>	Unity-gain bandwidth			2.7	3		MHz
Vn	Equivalent input noise voltage	f = 1 kHz,	R <sub>S</sub> =20Ω		18		nV/√ <del>Hz</del>
In	Equivalent input noise current	f = 1 kHz			0.01		pA/√ <del>Hz</del>



<sup>‡</sup> At least 90% of the devices meet this limit for  $\alpha_{VIO}$ .

<sup>§</sup> Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperatures as close to the ambient temperature as possible.

NOTE 2: Supply-voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously.

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